

Yukiharu Uraoka

List of Publications by Year in descending order

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71
docs citations

71
times ranked

1660
citing authors

#	ARTICLE	IF	CITATIONS
1	Forming Fe nanocrystals by reduction of ferritin nanocores for metal nanocrystal memory. AIP Advances, 2022, 12, 055029.	1.3	0
2	A 3D Vertical-Channel Ferroelectric/Anti-Ferroelectric FET With Indium Oxide. IEEE Electron Device Letters, 2022, 43, 1227-1230.	3.9	14
3	Orientation dependent etching of polycrystalline diamond by hydrogen plasma. Applied Physics Letters, 2022, 121, 021903.	3.3	1
4	Recover possibilities of potential induced degradation caused by the micro-cracked locations in p-type crystalline silicon solar cells. Progress in Photovoltaics: Research and Applications, 2021, 29, 423-432.	8.1	10
5	Performance Enhancement of Solution-Processed In-Zn-O Thin-film Transistors via Low-Temperature Wet Annealing Ambients. , 2021, , .		0
6	Improved Thermoelectric Power Factor of InGaZnO/SiO ₂ , Thin Film Transistor via Gate-Tunable Energy Filtering. IEEE Electron Device Letters, 2021, 42, 1236-1239.	3.9	7
7	The Influence of Ga-OH Bond at Initial GaN Surface on the Electrical Characteristics of SiO ₂ /GaN Interface. Physica Status Solidi (B): Basic Research, 2020, 257, 1900368.	1.5	7
8	Evaluate Fixed Charge and Oxide-Trapped Charge on SiO ₂ /GaN Metal-Oxide-Semiconductor Structure Before and After Postannealing. Physica Status Solidi (B): Basic Research, 2020, 257, 1900444.	1.5	8
9	Thermoelectric Si ^x Ge _{1-x} and Ge epitaxial films on Si(001) with controlled composition and strain for group IV element-based thermoelectric generators. Applied Physics Letters, 2020, 117, .	3.3	19
10	Enhanced Thermoelectric Transport and Stability in Atomic Layer Deposited-HfO ₂ /ZnO and TiO ₂ /ZnO-Sandwiched Multilayer Thin Films. ACS Applied Materials & Interfaces, 2020, 12, 49210-49218.	8.0	16
11	High-Performance Fully Solution-Processed Oxide Thin-Film Transistors via Photo-Assisted Role Tuning of InZnO. ACS Applied Electronic Materials, 2020, 2, 2398-2407.	4.3	17
12	Electrical and Optical Properties of Nickel-Oxide Films for Efficient Perovskite Solar Cells. Small Methods, 2020, 4, 2000454.	8.6	37
13	Improvement in Bias Stress Stability of Solution-Processed Amorphous InZnO Thin-Film Transistors via Low-Temperature Photosensitive Passivation. IEEE Electron Device Letters, 2020, 41, 1372-1375.	3.9	12
14	Unseeded Crystal Growth of (100)-Oriented Grain-Boundary-Free Si Thin-Film by a Single Scan of the CW-Laser Lateral Crystallization of a-Si on Insulator. Crystals, 2020, 10, 405.	2.2	7
15	Development of High-Reliability and -Stability Chemical Sensors Based on an Extended-Gate Type Amorphous Oxide Semiconductor Thin-Film Transistor. ACS Applied Electronic Materials, 2020, 2, 405-408.	4.3	8
16	Unique degradation under AC stress in high-mobility amorphous In ^W Zn ^O thin-film transistors. Applied Physics Express, 2020, 13, 054003.	2.4	13
17	Photo-assisted Processing of Amorphous Gallium Oxide (a-GaOx) Thin Film for Flexible and Transparent Device Application. , 2020, , .		1
18	High reliability InGaZnO TFT by inductively coupled plasma sputtering system. , 2019, , .		0

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19	Segregation-free bromine-doped perovskite solar cells for IoT applications. RSC Advances, 2019, 9, 32833-32838.	3.6	13
20	Thermoelectric Conversion Device Using Ga-Sn-O Thin Film Prepared by Mist CVD Method. , 2018, , .		0
21	Reliability Enhancement of Solution Processed Amorphous In-Zn-O Thin-Film Transistors via a Low Temperature (180 Å°C) Solution Processed Passivation. , 2018, , .		0
22	Low temperature cured poly-siloxane passivation for highly reliable <i>a</i> -InGaZnO thin-film transistors. Applied Physics Letters, 2018, 112, .	3.3	18
23	Instantaneous Semiconductor-to-Conductor Transformation of a Transparent Oxide Semiconductor <i>a</i> -InGaZnO at 45 Å°C. ACS Applied Materials & Interfaces, 2018, 10, 24590-24597.	8.0	12
24	Self-Heating Suppressed Structure of <i>a</i> -IGZO Thin-Film Transistor. IEEE Electron Device Letters, 2018, 39, 1322-1325.	3.9	9
25	Significant mobility improvement of amorphous In-Ga-Zn-O thin-film transistors annealed in a low temperature wet ambient environment. Applied Physics Letters, 2018, 112, 193501.	3.3	20
26	Threshold Voltage Control of In-Ga-Zn-O TFT without Thermal Annealing Process by Inductively Coupled Plasma Sputtering System. , 2018, , .		0
27	H and Au diffusion in high mobility <i>a</i> -InGaZnO thin-film transistors via low temperature KrF excimer laser annealing. Applied Physics Letters, 2017, 110, .	3.3	14
28	Biotemplated Synthesis of TiO ₂ -Coated Gold Nanowire for Perovskite Solar Cells. ACS Omega, 2017, 2, 5478-5485.	3.5	6
29	Fabrication of Nanoshell-Based 3D Periodic Structures by Templating Process using Solution-derived ZnO. Nanoscale Research Letters, 2017, 12, 419.	5.7	16
30	Effect of Gold Nanoparticle Distribution in TiO ₂ on the Optical and Electrical Characteristics of Dye-Sensitized Solar Cells. Nanoscale Research Letters, 2017, 12, 513.	5.7	27
31	High-density carrier-accumulated and electrically stable oxide thin-film transistors from ion-gel gate dielectric. Scientific Reports, 2016, 5, 18168.	3.3	24
32	Selection of a novel peptide aptamer with high affinity for TiO ₂ -nanoparticle through a direct electroporation with TiO ₂ -binding phage complexes. Journal of Bioscience and Bioengineering, 2016, 122, 528-532.	2.2	5
33	Numerical modeling of device structure for FeS₂ thin film solar cells. , 2016, , .		0
34	Internal resistance of perovskite solar cells under low illuminance conditions. , 2016, , .		0
35	Charge effects of ultrafine FET with nanodot type floating gate. , 2016, , .		1
36	Characteristics of Perovskite Solar Cells under Low-Illuminance Conditions. Journal of Physical Chemistry C, 2016, 120, 18986-18990.	3.1	43

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37	Interface Optoelectronics Engineering for Mechanically Stacked Tandem Solar Cells Based on Perovskite and Silicon. ACS Applied Materials & Interfaces, 2016, 8, 33553-33561.	8.0	36
38	Creating Reversible p-n Junction on Graphene through Ferritin Adsorption. ACS Applied Materials & Interfaces, 2016, 8, 8192-8200.	8.0	12
39	Analysis of thermoelectric properties of amorphous InGaZnO thin film by controlling carrier concentration. AIP Advances, 2015, 5, .	1.3	44
40	Unseeded growth of poly-crystalline Ge with (111) surface orientation on insulator by pulsed green laser annealing. , 2015, , .		0
41	Highly reliable passivation layer for a-InGaZnO thin-film transistors fabricated using polysilsesquioxane. Materials Research Society Symposia Proceedings, 2014, 1633, 139-144.	0.1	6
42	Controlled charged amino acids of Ti-binding peptide for surfactant-free selective adsorption. Colloids and Surfaces B: Biointerfaces, 2014, 118, 25-30.	5.0	7
43	Hydrogen behavior from ALD Al ₂ O ₃ passivation layer for amorphous InGaZnO TFTs. , 2014, , .		0
44	Oxidation of graphene film by non-thermal treatment for new sensing devices. , 2014, , .		0
45	Effects of Si and Ti impurities on electrical properties of sol-gel-derived amorphous SrTa ₂ O ₆ thin films by UV/O ₃ treatment. Applied Physics A: Materials Science and Processing, 2013, 112, 425-430.	2.3	3
46	Thermal reversibility in electrical characteristics of ultraviolet/ozone-treated graphene. Applied Physics Letters, 2013, 103, 063107.	3.3	14
47	Comparison between ZnO films grown by plasma-assisted atomic layer deposition using H ₂ O plasma and O ₂ plasma as oxidant. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2013, 31, 01A142.	2.1	15
48	Characterizations of Al ₂ O ₃ gate dielectric deposited on n-GaN by plasma-assisted atomic layer deposition. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1426-1429.	0.8	19
49	Thermal distribution in amorphous InSnZnO thin-film transistor. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1561-1564.	0.8	9
50	Low-temperature fabrication of solution-processed InZnO thin-film transistors with Si impurities by UV/O ₃ -assisted annealing. AIP Advances, 2012, 2, .	1.3	20
51	Effect of high-pressure deuterium oxide annealing on Al ₂ O ₃ deposited by plasma-assisted atomic layer deposition at low temperature. , 2012, , .		0
52	Characterization of graphene based field effect transistors using nano probing microscopy. , 2012, , .		0
53	Floating Gate Memory With Biomineralized Nanodots Embedded in HfO ₂ . IEEE Nanotechnology Magazine, 2011, 10, 576-581.	2.0	2
54	Fabrication of PbTiO ₃ and Pt self-organized nanocrystal array structure on atomically flat sapphire. , 2011, , .		0

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55	Voltage Linearity and Leakage Currents of Crystalline and Amorphous SrTa ₂ O ₆ Thin Films Fabricated by Sol-Gel Method. <i>Ferroelectrics</i> , 2011, 421, 82-87.	0.6	2
56	OS06-2-3 Carbon nanotubes-embedded MEMS resonator device for hydrogen gas sensing system. The Abstracts of ATEM International Conference on Advanced Technology in Experimental Mechanics Asian Conference on Experimental Mechanics, 2011, 2011.10, _OS06-2-3-.	0.0	0
57	Characterization of local electrical properties of polycrystalline silicon thin films and hydrogen termination effect by conductive atomic force microscopy. <i>Applied Physics Letters</i> , 2009, 94, 182104.	3.3	6
58	ZnO Thin Film Transistors Fabricated by Atomic Layer Deposition Method. <i>Materials Research Society Symposia Proceedings</i> , 2009, 1201, 237.	0.1	2
59	Comprehensive study of electroluminescence in multicrystalline silicon solar cells. <i>Journal of Applied Physics</i> , 2009, 106, .	2.5	26
60	Analysis of Anomalous Charge-Pumping Characteristics on 4H-SiC MOSFETs. <i>IEEE Transactions on Electron Devices</i> , 2008, 55, 2013-2020.	3.0	34
61	Low Temperature Synthesis of Nanocrystalline Silicon and Silicon Oxide Films by Plasma Chemical Vapor Deposition. <i>Materials Research Society Symposia Proceedings</i> , 2008, 1066, 1.	0.1	0
62	Feasible control of laser doping profiles in silicon solar cell processing using multiple excitation wavelengths. <i>Conference Record of the IEEE Photovoltaic Specialists Conference</i> , 2008, , .	0.0	2
63	Floating nanodot gate memory fabrication with biomaterialized nanodot as charge storage node. <i>Journal of Applied Physics</i> , 2008, 103, .	2.5	61
64	Anomalous anisotropic channel mobility on trench sidewalls in 4H-SiC trench-gate metal-oxide-semiconductor field-effect transistors fabricated on 8° off substrates. <i>Applied Physics Letters</i> , 2007, 90, 042102.	3.3	50
65	Electron confinement in a metal nanodot monolayer embedded in silicon dioxide produced using ferritin protein. <i>Applied Physics Letters</i> , 2006, 88, 023108.	3.3	54
66	Floating Nanodot Gate Memory Devices Based on Biomaterialized Inorganic Nanodot Array as a Storage Node. <i>Japanese Journal of Applied Physics</i> , 2006, 45, L1-L3.	1.5	100
67	Experimental investigation of tunnel oxide thickness on charge transport through Si nanocrystal dot floating gate memories. <i>Journal of Vacuum Science & Technology B</i> , 2006, 24, 1271.	1.3	18
68	Charging and Coulomb staircase effects in silicon nanodisk structures fabricated by defect-free Cl neutral beam etching process. <i>Applied Physics Letters</i> , 2006, 89, 233127.	3.3	19
69	Hot Carrier Effect in UltraThin Gate Oxide Metal Oxide Semiconductor Field Effect Transistor. <i>Japanese Journal of Applied Physics</i> , 2005, 44, 5889-5892.	1.5	3
70	Photographic surveying of minority carrier diffusion length in polycrystalline silicon solar cells by electroluminescence. <i>Applied Physics Letters</i> , 2005, 86, 262108.	3.3	436
71	Novel Method for Making Nanodot Arrays Using a Cage-like Protein. <i>Japanese Journal of Applied Physics</i> , 2003, 42, L398-L399.	1.5	54